

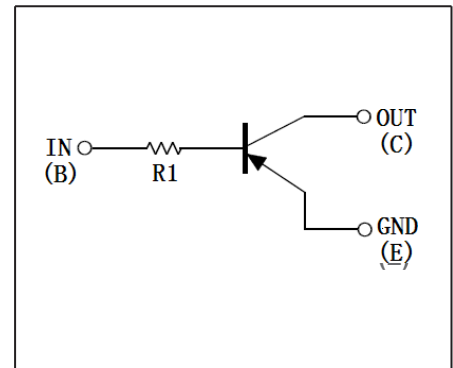
DTA115TM/DTA115TE/DTA115TUA DTA115TKA/DTA115TCA/DTA115TSA

DIGITAL TRANSISTOR (PNP)

FEATURES

- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors(see equivalent circuit)
- The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input.They also have the advantage of almost completely eliminating parasitic effects
- Only the on/off conditions need to be set for operation, making device design easy

• Equivalent Circuit



Part Number	MARKING ⁽¹⁾	Package	Packing Method	Pack Quantity
DTA115TM	99	SOT-723	Reel	8000pcs/Reel
DTA115TE	99	SOT-523	Reel	3000pcs/Reel
DTA115TUA	99	SOT-323	Reel	3000pcs/Reel
DTA115TKA	99	SOT-23-3L	Reel	3000pcs/Reel
DTA115TCA	99	SOT-23	Reel	3000pcs/Reel
DTA115TSA	A115 ⁽²⁾ T•XXX	TO-92S	Bulk	1000pcs/Bag
DTA115TSA-TA	A115 ⁽²⁾ T•XXX	TO-92S	Tape	3000pcs/Box

Notes: (1). Solid dot = Green molding compound device, if none, the normal device.

(2). XXX=Code

MAXIMUM RATINGS(Ta=25 °C unless otherwise noted)

Symbol	Parameter	Limits(DTA115T□)						Unit
		M	E	UA	KA	CA	SA	
V _{CBO}	Collector-Base Voltage	-50						V
V _{CEO}	Collector-Emitter Voltage	-50						V
V _{EBO}	Emitter-Base Voltage	-5						V
I _C	Collector Current	-100						mA
P _D	Power Dissipation	100	150	200	200	200	300	mW
T _J , T _{stg}	Operation Junction and Storage Temperature Range	-55~+150						°C

ELECTRICAL CHARACTERISTICS (Ta=25 °C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-50μA, I _E =0	-50			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-50μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-50V, I _E =0			-0.5	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-4V, I _C =0			-0.5	μA
DC current gain	h _{FE}	V _{CE} =-5V, I _C =-1mA	100		600	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-1mA, I _B =-0.1mA			-0.3	V
Transition frequency	f _T	V _{CE} =-10V, I _E =5mA, f=100MHz		250		MHz
Input resistor	R ₁		70	100	130	kΩ

Static Characteristic
